



## DMP25H18DLFDE

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D max</sub> T <sub>A</sub> = +25 ℃
-250V	14Ω @ V <sub>GS</sub> = -10V	-0.26A
	18Ω @ V <sub>GS</sub> = -3.5V	-0.23A

## Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

U-DFN2020-6

Bottom View

## **Applications**

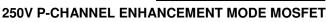
General Purpose Interfacing Switch

Pin1

- Load Switching
- Battery Management Application
- Power Management Functions

#### 

Pin Out Bottom View



#### Features

- 0.6mm Profile Ideal for Low-Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

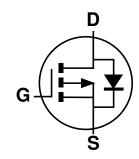
## **Mechanical Data**

• Case: U-DFN2020-6

2

3

- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0065 grams (Approximate)



Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Quantity per Reel
DMP25H18DLFDE-7	H8	7	3,000
DMP25H18DLFDE-13	H8	13	10,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

#### U-DFN2020-6



 $\begin{array}{l} \mathsf{H8} = \mathsf{Product Type Marking Code} \\ \mathsf{YM} = \mathsf{Date Code Marking} \\ \mathsf{Y} = \mathsf{Year} \ (\mathsf{ex: B} = 2014) \\ \mathsf{M} = \mathsf{Month} \ (\mathsf{ex: 9} = \mathsf{September}) \end{array}$ 

Data	Code	Kov
Dale	Code	nev

Year	2014		2015	2016		2017	2018		2019	2020		2021
Code	В		С	D		E	F		G	Н		
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



#### **Maximum Ratings** (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V <sub>DSS</sub>	-250	V		
Gate-Source Voltage	V <sub>GSS</sub>	±40	V		
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady $T_A = +25 \degree$ State $T_A = +70 \degree$			ID	-0.26 -0.21	А
Pulsed Drain Current (10 $\mu$ s pulse, duty cycle $\leq$ 1%)	I <sub>DM</sub>	-0.8	A		
Maximum Body Diode Continuous Current (Note 6)	Is	1.2	А		

# **Thermal Characteristics**

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 5)	D-	0.6	W	
Total Power Dissipation	(Note 6)	PD	1.4		
Thermal Desistance, Junction to Ambient	(Note 5)		191		
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>θJA</sub>	86	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R <sub>θJC</sub>	17		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

## Electrical Characteristics (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	Symbol	WIIII	тур	Max	Unit	Test condition
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-250	_	_	V	$V_{GS} = 0V, I_{D} = -1mA$
Zero Gate Voltage Drain Current $T_J = +25^{\circ}$ C	I <sub>DSS</sub>		_	-1	μA	$V_{DS} = -250V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 40V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)	-000					
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	-1.7	-2.5	V	$V_{DS} = V_{GS}, I_D = -1mA$
Obstile Desile Oscenes On Desiletance			10	14	0	V <sub>GS</sub> = -10V, I <sub>D</sub> = -200mA
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	13	18	Ω	$V_{GS} = -3.5V, I_D = -100mA$
Diode Forward Voltage	V <sub>SD</sub>		-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -200mA$
DYNAMIC CHARACTERISTICS (Note 8)						÷
Input Capacitance	Ciss	—	81	—	pF	
Output Capacitance	Coss		14	—	pF	└ V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, - f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	4	—	pF	
Gate Resistance	Rg	—	13	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	—	2.8	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	0.3	—	nC	V <sub>DS</sub> = -25V, I <sub>D</sub> = -200mA
Gate-Drain Charge	Q <sub>gd</sub>	—	0.6	—	nC	7
Turn-On Delay Time	t <sub>D(on)</sub>	—	7.5	—	ns	
Turn-On Rise Time	tr	—	25	—	ns	V <sub>DS</sub> = -30V, I <sub>D</sub> = -200mA
Turn-Off Delay Time	t <sub>D(off)</sub>	—	124	—	ns	$V_{GS} = -10V, R_G = 50\Omega$
Turn-Off Fall Time	tf	_	95	—	ns	
Reverse Recovery Time	t <sub>rr</sub>	_	85	—	ns	
Reverse Recovery Charge	Qrr	—	294		uC	- I <sub>F</sub> = -1.0A, di/dt = 100A/μs

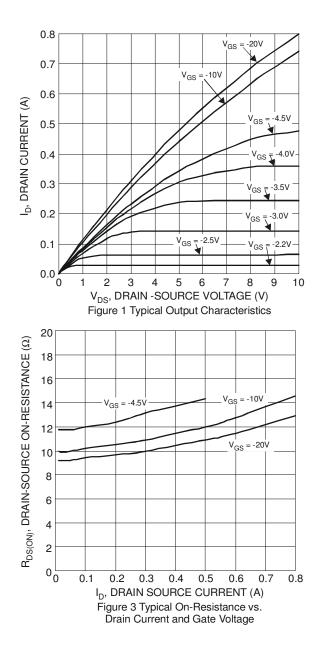
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

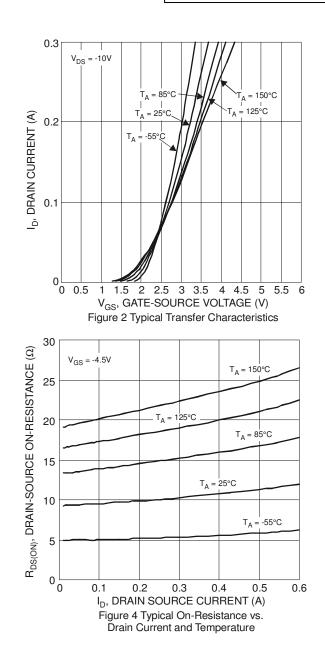
Device mounted on FR-4 substrate PC board, 2cz copper, with thermal vias to bottom layer 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.

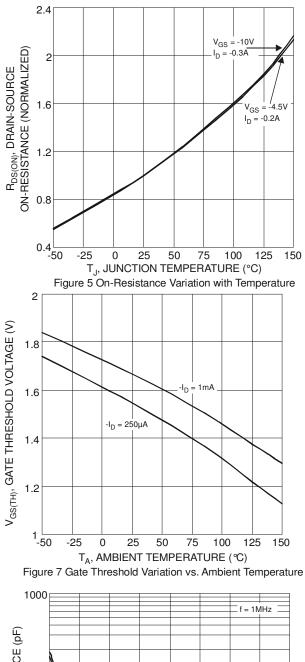
## DMP25H18DLFDE

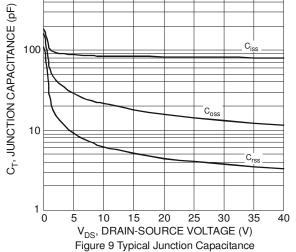


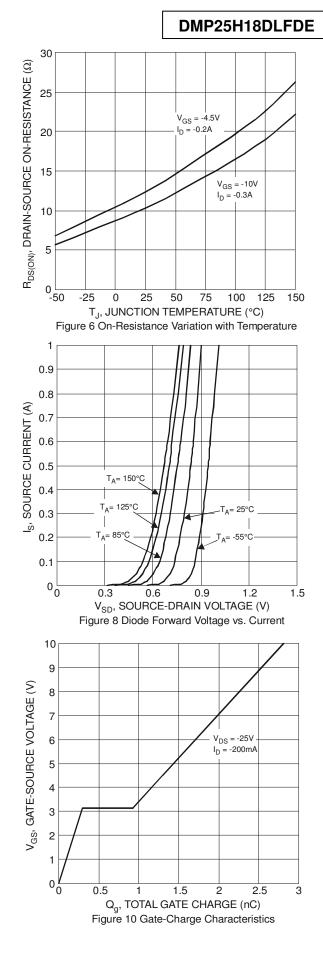


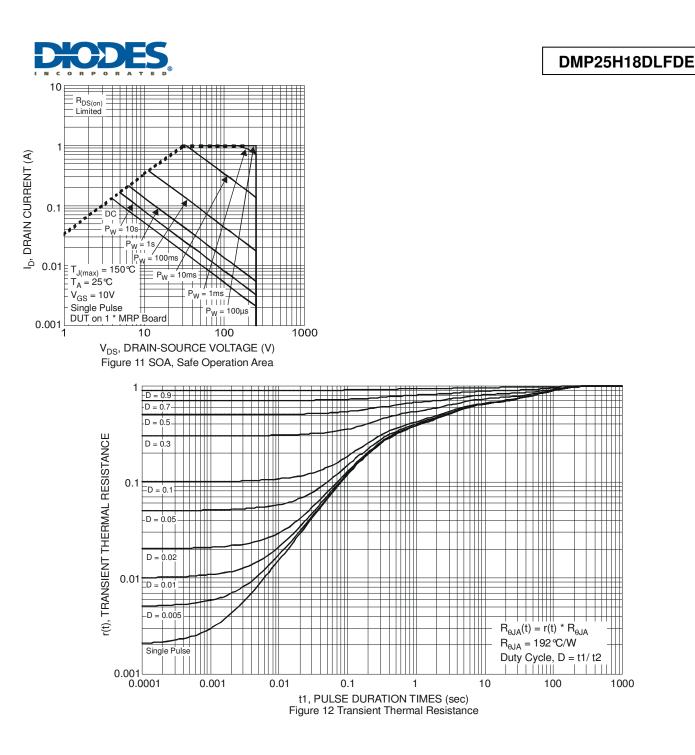








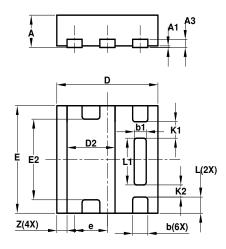






## **Package Outline Dimensions**

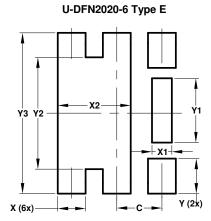
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-DFN2020-6 Type E						
Dim	Min	Max	Тур			
Α	0.57	0.63	0.60			
A1	0	0.05	0.03			
A3		I	0.15			
b	0.25	0.35	0.30			
b1	0.185	0.285	0.235			
D	1.95	2.05	2.00			
D2	0.85	1.05	0.95			
E	1.95	2.05	2.00			
E2	1.40	1.60	1.50			
е	—		0.65			
L	0.25	0.35	0.30			
L1	0.82	0.92	0.87			
K1	_		0.305			
K2	_		0.225			
Z	_		0.20			
All	Dimens	ions in r	nm			

## **Suggested Pad Layout**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300



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